

IN THE SPECIFICATION

Please amend the specification as follows:

Replace the paragraph on page 13, between lines 11-20 of the specification with the following:

In a next step, as shown in FIG. 5c, the layers 22 of the second material on the first surface 12 of the elastomeric stamp 10 are brought into contact with a substrate 500, which may be part of an electronic device or a part of an intermediate component for such a device. The substrate 500, which for instance may be a silicon wafer, carries an additional layer 502 for receiving the molecular ink 520 in a pattern dictated by the shape of the elastomeric stamp 10. When using thiol-based inks 520, the additional layer ~~402~~502 preferably comprises a coinage metal, e.g., a noble metal layer such as a gold layer having a thickness of 10-50 nm, although the choice of other metals and other thicknesses for the layer 502 are also feasible.

Replace the paragraph on page 14, between lines 8-16 of the specification with the following:

At this point, it is emphasized that if no further barrier layer 24 is present on the second surface 14, gas phase diffusion of the ink 520 from the second surface 14 as well as from the third surface 16 may also take place, as indicated by the dashed arrows in ~~Fig. 4c~~ Fig. 5c. The gas phase diffusion becomes more pronounced with increasing ink vapour pressures at the printing temperature, i.e., with inks having boiling points in the vicinity of the printing temperature. It will be understood that this is an unwanted effect when hollow or other high-definition features are required, because the gas phase diffusion can cause blurring of the desired pattern.